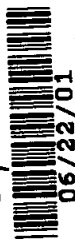


PATENT NUMBER

JC872 U.S. PTO
09/887910

06/22/01

	Subclass	ISSUE CLASSIFICATION
	Class	

U.S. UTILITY Patent Application

O.I.P.E. <i>HP</i> SCANNED <i>Ed</i> Q.A. <i>TM</i>	PATENT DATE
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APPLICATION NO. 09/887910	CONT/PRIOR	CLASS 438	SUBCLASS 73	ART UNIT 2812	EXAMINER Anya
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TITLE APPLICANTS

Jack Hwang
Mitchell Taylor

Method of making a semiconductor transistor by implanting ions into a gate dielectric layer thereof

PTO-2040
12/99

ISSUING CLASSIFICATION

ORIGINAL		CROSS REFERENCE(S)							
CLASS	SUBCLASS	CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)						
INTERNATIONAL CLASSIFICATION									

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<input type="checkbox"/> TERMINAL DISCLAIMER	DRAWINGS			CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.
<input type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed.	_____ (Assistant Examiner) _____ (Date)			NOTICE OF ALLOWANCE MAILED	
<input type="checkbox"/> The term of this patent shall not extend beyond the expiration date of U.S Patent. No. _____	_____ (Primary Examiner) _____ (Date)			ISSUE FEE	
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